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DUAL DIGIT LED DISPLAY (0.40 Inch)

LDD405/6SBKS-XXN/P10

DATA SHEET

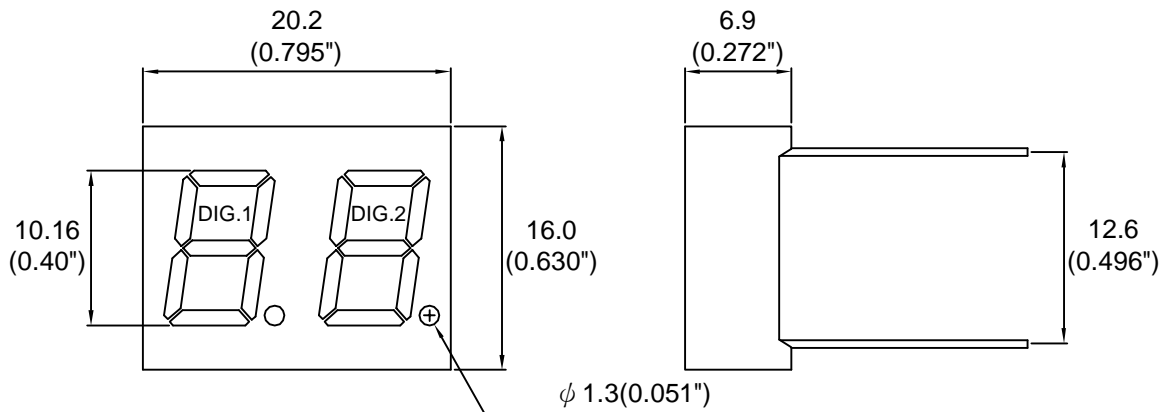
DOC. NO : QW0905-LDD405/6SBKS-XXN/P10

REV. : A

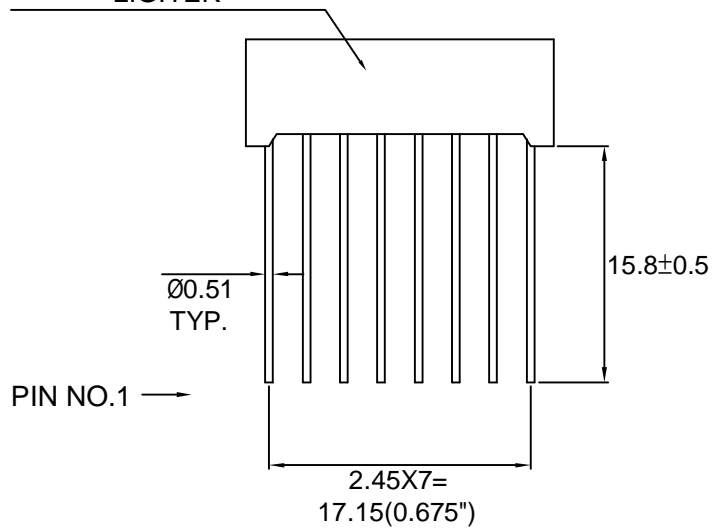
DATE : 01- Nov. - 2005



Package Dimensions



LDD405/6SBKS-XXN/P10
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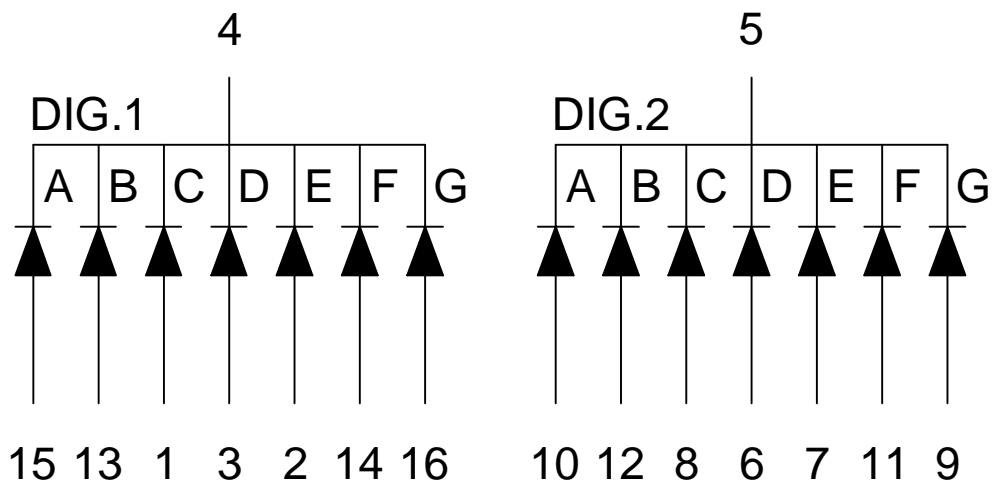


Note : 1.All dimension are in millimeters and (Inch) tolerance is $\pm 0.25(0.01")$ unless otherwise noted.
2.Specifications are subject to change without notice.

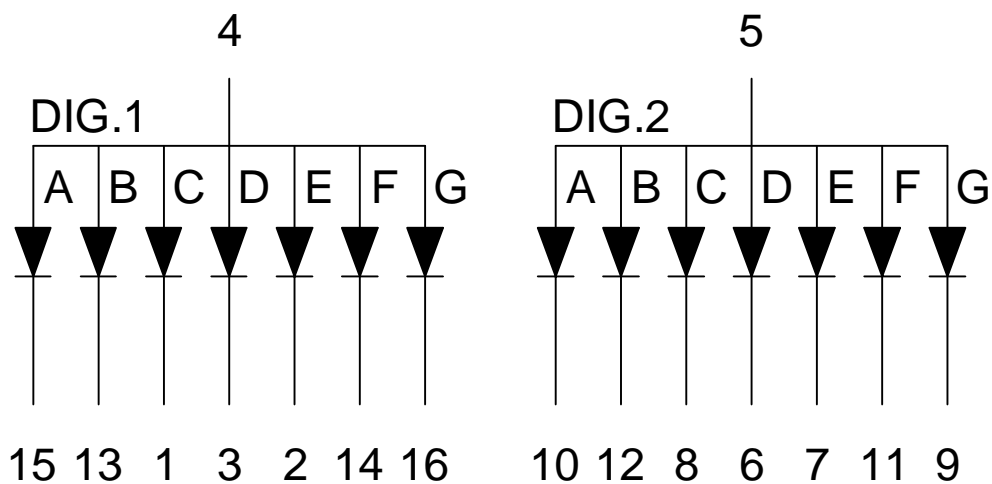


Internal Circuit Diagram

LDD405SBKS-XXN/P10



LDD406SBKS-XXN/P10



**Electrical Connection**

PIN NO.	LDD405SBKS-XXN/P10	PIN NO.	LDD406SBKS-XXN/P10
1	Anode C Dig.1	1	Cathode C Dig.1
2	Anode E Dig.1	2	Cathode E Dig.1
3	Anode D Dig.1	3	Cathode D Dig.1
4	Common Cathode Dig.1	4	Common Anode Dig.1
5	Common Cathode Dig.2	5	Common Anode Dig.2
6	Anode D Dig.2	6	Cathode D Dig.2
7	Anode E Dig.2	7	Cathode E Dig.2
8	Anode C Dig.2	8	Cathode C Dig.2
9	Anode G Dig.2	9	Cathode G Dig.2
10	Anode A Dig.2	10	Cathode A Dig.2
11	Anode F Dig.2	11	Cathode F Dig.2
12	Anode B Dig.2	12	Cathode B Dig.2
13	Anode B Dig.1	13	Cathode B Dig.1
14	Anode F Dig.1	14	Cathode F Dig.1
15	Anode A Dig.1	15	Cathode A Dig.1
16	Anode G Dig.1	16	Cathode G Dig.1

**Absolute Maximum Ratings at Ta=25 °C**

Parameter	Symbol	Ratings	UNIT
		SBKS	
Forward Current Per Chip	IF	30	mA
Peak Forward Current Per Chip (Duty 1/10,0.1ms Pulse Width)	IFP	100	mA
Power Dissipation Per Chip	PD	120	mW
Reverse Current Per Any Chip	Ir	50	μA
Electrostatic Discharge(*)	ESD	500	V
Operating Temperature	Topr	-25 ~ +85	°C
Storage Temperature	Tstg	-25 ~ +85	°C

Solder Temperature 1/16 Inch Below Seating Plane For 3 Seconds At 260 °C

* Static Electricity or power surge will damage the LED. Use of a conductive wrist band or anti-electrostatic glove is recommended when handling these LED. All devices, equipment and machinery must be properly grounded.

Part Selection And Application Information(Ratings at 25°C)

PART NO	CHIP		common cathode or anode	λ D (nm)	Δ λ (nm)	Electrical				IV-M
	Material	Emitted				Vf(v)		Iv(mcd)		
						Typ.	Max.	Min.	Typ.	
LDD405SBKS-XXN/P10	InGaN/SiC	Blue	Common Cathode	475	26	3.5	4.2	7.2	12.8	2:1
LDD406SBKS-XXN/P10			Common Anode							

Note : 1.The forward voltage data did not including ±0.1V testing tolerance.

2. The luminous intensity data did not including ±15% testing tolerance.



Test Condition For Each Parameter

Parameter	Symbol	Unit	Test Condition
Forward Voltage Per Chip	V _f	volt	I _f =20mA
Luminous Intensity Per Chip	I _v	mcd	I _f =10mA
Dominant Wavelength	λ_D	nm	I _f =20mA
Spectral Line Half-Width	$\Delta \lambda$	nm	I _f =20mA
Reverse Current Any Chip	I _r	μA	V _r =5V
Luminous Intensity Matching Ratio	IV-M		



Typical Electro-Optical Characteristics Curve

SBK-S CHIP

Fig.1 Forward current vs. Forward Voltage

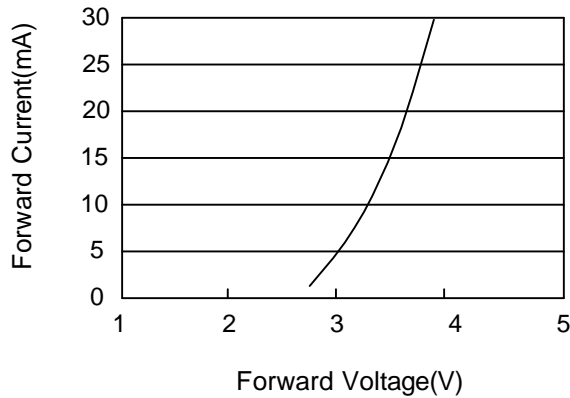


Fig.2 Relative Intensity vs. Forward Current

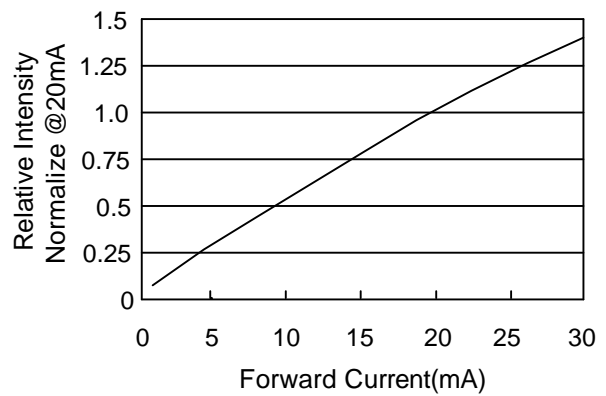


Fig.3 Forward Current vs. Temperature

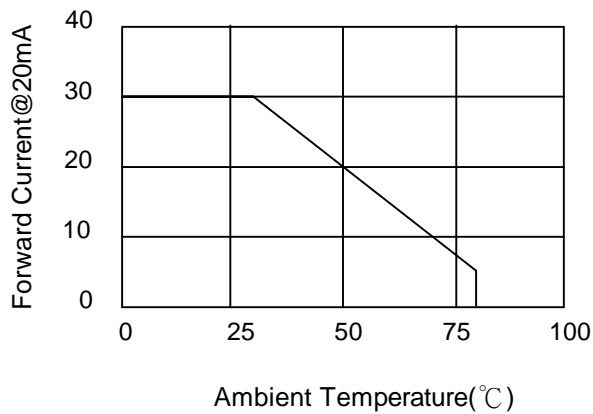
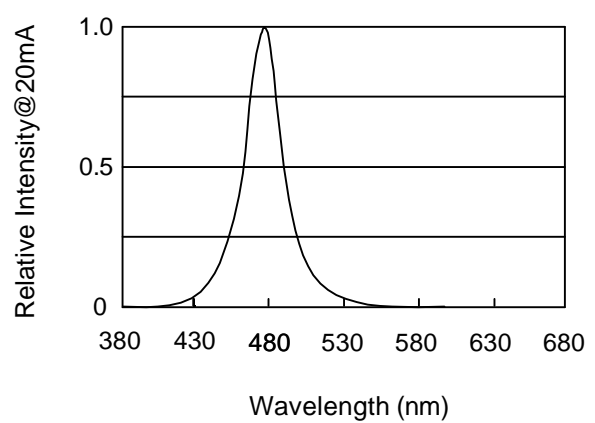


Fig.4 Relative Intensity vs. Wavelength





Reliability Test:

Test Item	Test Condition	Description	Reference Standard
Operating Life Test	1.Under Room Temperature 2.If=10mA 3.t=1000 hrs (-24hrs, +72hrs)	This test is conducted for the purpose of detemining the resisance of a part in electrical and themal stressed.	MIL-STD-750: 1026 MIL-STD-883: 1005 JIS C 7021: B-1
High Temperature Storage Test	1.Ta=105 °C±5°C 2.t=1000 hrs (-24hrs, +72hrs)	The purpose of this is the resistance of the device which is laid under ondition of high temperature for hours.	MIL-STD-883:1008 JIS C 7021: B-10
Low Temperature Storage Test	1.Ta=-40 °C±5°C 2.t=1000 hrs (-24hrs, +72hrs)	The purpose of this is the resistance of the device which is laid under condition of low temperature for hours.	JIS C 7021: B-12
High Temperature High Humidity Test	1.Ta=65 °C±5°C 2.RH=90%-95% 3.t=240hrs ±2hrs	The purpose of this test is the resistance of the device under tropical for hous.	MIL-STD-202:103B JIS C 7021: B-11
Thermal Shock Test	1.Ta=105 °C±5°C & -40 °C±5°C (10min) (10min) 2.total 10 cycles	The purpose of this is the resistance of the device to sudden extreme changes in high and low temperature.	MIL-STD-202: 107D MIL-STD-750: 1051 MIL-STD-883: 1011
Solder Resistance Test	1.T.Sol=260 °C±5°C 2.Dwell time= 10 ±1sec.	This test intended to determine the thermal characteristic resistance of the device to sudden exposures at extreme changes in temperature when soldering the lead wire.	MIL-STD-202: 210A MIL-STD-750: 2031 JIS C 7021: A-1
Solderability Test	1.T.Sol=230 °C±5°C 2.Dwell time=5 ±1sec	This test intended to see soldering well performed or not.	MIL-STD-202: 208D MIL-STD-750: 2026 MIL-STD-883: 2003 JIS C 7021: A-2